

## Features

- Very high speed: 45 ns
- Temperature ranges
  - Industrial: -40°C to +85°C
  - Automotive-A: -40°C to +85°C
  - Automotive-E: -40°C to +125°C
- Wide voltage range: 2.20V–3.60V
- Pin compatible with CY62137CV/CV25/CV30/CV33, CY62137V, and CY62137EV30
- Ultra low standby power
  - Typical standby current: 1  $\mu$ A
  - Maximum standby current: 5  $\mu$ A (Industrial)
- Ultra low active power
  - Typical active current: 1.6 mA at f = 1 MHz (45 ns speed)
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- Automatic power down when deselected
- CMOS for optimum speed and power
- Byte power down feature
- Available in Pb free 48-Ball VFBGA and 44-pin TSOP II package

## Functional Description

The CY62137FV30 is a high performance CMOS static RAM organized as 128K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This

is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption by 90% when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ( $\overline{CE}$  HIGH or both  $\overline{BLE}$  and  $\overline{BHE}$  are HIGH). The input and output pins ( $IO_0$  through  $IO_{15}$ ) are placed in a high impedance state in the following conditions:

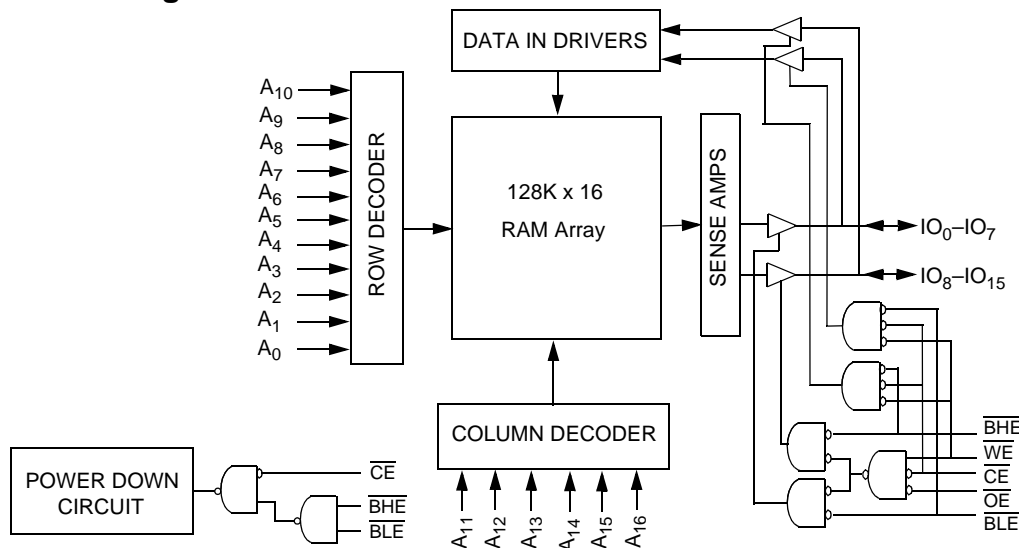
- Deselected ( $\overline{CE}$  HIGH)
- Outputs are disabled ( $\overline{OE}$  HIGH)
- Both Byte High Enable and Byte Low Enable are disabled ( $\overline{BHE}$ ,  $\overline{BLE}$  HIGH)
- Write operation is active ( $\overline{CE}$  LOW and  $\overline{WE}$  LOW)

Write to the device by taking Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from  $IO$  pins ( $IO_0$  through  $IO_7$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{16}$ ). If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from  $IO$  pins ( $IO_8$  through  $IO_{15}$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{16}$ ).

Read from the device by taking Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW, while forcing the Write Enable ( $\overline{WE}$ ) HIGH. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from the memory location specified by the address pins appear on  $IO_0$  to  $IO_7$ . If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from memory appears on  $IO_8$  to  $IO_{15}$ . See the "Truth Table" on page 9 for a complete description of read and write modes.

For best practice recommendations, refer to the Cypress application note [AN1064, SRAM System Guidelines](#).

## Logic Block Diagram



## Product Portfolio

Product	Range	V <sub>CC</sub> Range (V)			Speed (ns)	Power Dissipation					
						Operating I <sub>CC</sub> (mA)				Standby I <sub>SB2</sub> (μA)	
						f = 1 MHz		f = f <sub>max</sub>			
		Min	Typ <sup>[1]</sup>	Max		Typ <sup>[1]</sup>	Max	Typ <sup>[1]</sup>	Max	Typ <sup>[1]</sup>	Max
CY62137FV30LL	Ind'I/Auto-A	2.2V	3.0V	3.6V	45	1.6	2.5	13	18	1	5
	Auto-E	2.2V	3.0V	3.6V	55	2	3	15	25	1	20

## Pin Configuration

Figure 1. 48-Ball VFBGA Pinout<sup>[2, 3]</sup>

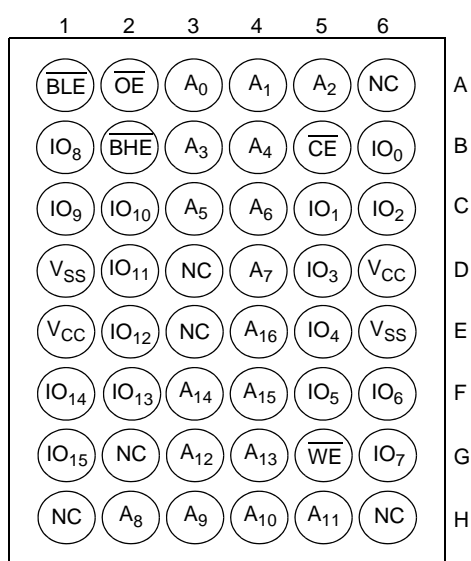
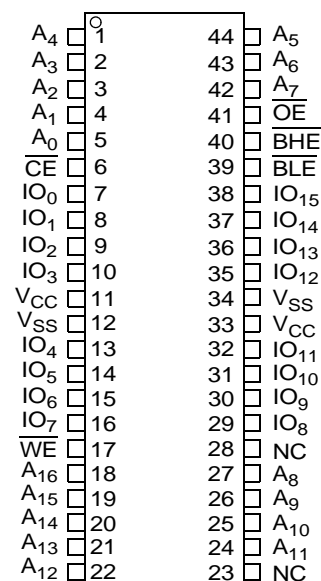


Figure 2. 44-Pin TSOP II<sup>[2]</sup>



### Notes

1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25°C.
2. NC pins are not connected on the die.
3. Pins D3, H1, G2, and H6 in the VFBGA package are address expansion pins for 4 Mb, 8 Mb, 16 Mb, and 32 Mb, respectively.

## Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ..... -65°C to + 150°C

Ambient Temperature with  
Power Applied ..... -55°C to + 125°C

Supply Voltage to Ground  
Potential ..... -0.3V to 3.9V

DC Voltage Applied to Outputs  
in High Z state <sup>[4, 5]</sup> ..... -0.3V to 3.9V

DC Input Voltage <sup>[4, 5]</sup> ..... -0.3V to 3.9V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V  
(MIL-STD-883, Method 3015)

Latch up Current ..... > 200 mA

## Operating Range

Device	Range	Ambient Temperature	V <sub>CC</sub> <sup>[6]</sup>
CY62137FV30LL	Ind'I/Auto-A	-40°C to +85°C	2.2V to 3.6V
	Auto-E	-40°C to +125°C	

## Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		45 ns (Ind'I/Auto-A)			55 ns (Auto-E)			Unit
				Min	Typ <sup>[1]</sup>	Max	Min	Typ <sup>[1]</sup>	Max	
V <sub>OH</sub>	Output HIGH Voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7	I <sub>OH</sub> = -0.1 mA	2.0			2.0			V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6	I <sub>OH</sub> = -1.0 mA	2.4			2.4			V
V <sub>OL</sub>	Output LOW Voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7	I <sub>OL</sub> = 0.1 mA			0.4			0.4	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6	I <sub>OL</sub> = 2.1 mA			0.4			0.4	V
V <sub>IH</sub>	Input HIGH Voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7		1.8		V <sub>CC</sub> + 0.3	1.8		V <sub>CC</sub> + 0.3	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6		2.2		V <sub>CC</sub> + 0.3	2.2		V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW Voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7		-0.3		0.6	-0.3		0.6	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6		-0.3		0.8	-0.3		0.8	V
I <sub>IX</sub>	Input Leakage Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>		-1		+1	-4		+4	μA
I <sub>OZ</sub>	Output Leakage Current	GND ≤ V <sub>O</sub> ≤ V <sub>CC</sub> , Output disabled		-1		+1	-4		+4	μA
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	f = f <sub>max</sub> = 1/t <sub>RC</sub>	V <sub>CC</sub> = V <sub>CC(max)</sub> I <sub>OUT</sub> = 0 mA CMOS levels		13	18		15	25	mA
		f = 1 MHz			1.6	2.5		2	3	
I <sub>SB1</sub>	Automatic CE Power Down Current – CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$ , $V_{IN} \geq V_{CC} - 0.2V$ , $V_{IN} \leq 0.2V$ $f = f_{max}$ (address and data only), $f = 0$ ( $\overline{OE}$ , $\overline{WE}$ , $\overline{BHE}$ , and $\overline{BLE}$ ), V <sub>CC</sub> = 3.60V			1	5		1	20	μA
I <sub>SB2</sub> <sup>[7]</sup>	Automatic CE Power Down Current – CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$ , $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$ , $f = 0$ , V <sub>CC</sub> = 3.60V			1	5		1	20	μA

## Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input Capacitance	T <sub>A</sub> = 25°C, f = 1 MHz, V <sub>CC</sub> = V <sub>CC(typ)</sub>	10	pF
C <sub>OUT</sub>	Output Capacitance		10	pF

### Notes

4. V<sub>IL(min)</sub> = -2.0V for pulse durations less than 20 ns.

5. V<sub>IH(max)</sub> = V<sub>CC</sub> + 0.75V for pulse durations less than 20 ns.

6. Full device AC operation assumes a minimum of 100 μs ramp time from 0 to V<sub>CC(min)</sub> and 200 μs wait time after V<sub>CC</sub> stabilization.

7. Only chip enable (CE) and byte enables (BHE and BLE) are tied to CMOS levels to meet the I<sub>SB2</sub> / I<sub>CCDR</sub> specification. Other inputs can be left floating.

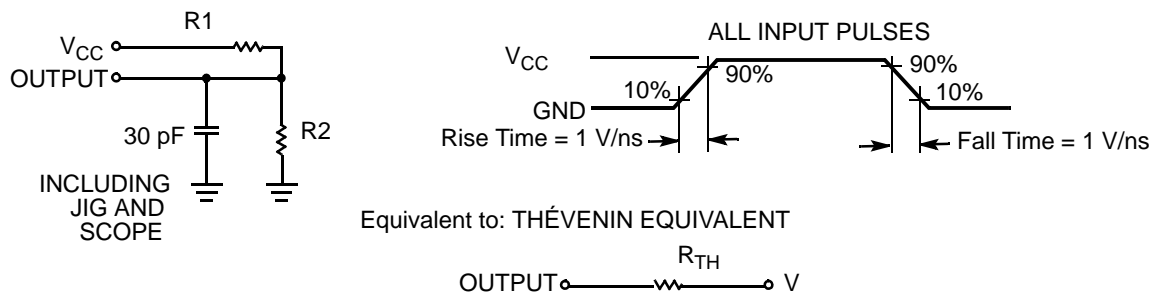
## Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	VFBGA	TSOP II	Unit
$\Theta_{JA}$	Thermal Resistance (Junction to Ambient)	Still air, soldered on a 3 × 4.5 inch, two layer printed circuit board	75	77	°C/W
$\Theta_{JC}$	Thermal Resistance (Junction to Case)		10	13	°C/W

## AC Test Loads and Waveforms

**Figure 3. AC Test Loads and Waveform**



Parameters	2.5V (2.2V to 2.7V)	3.0V (2.7V to 3.6V)	Unit
R1	16667	1103	$\Omega$
R2	15385	1554	$\Omega$
$R_{TH}$	8000	645	$\Omega$
$V_{TH}$	1.20	1.75	V

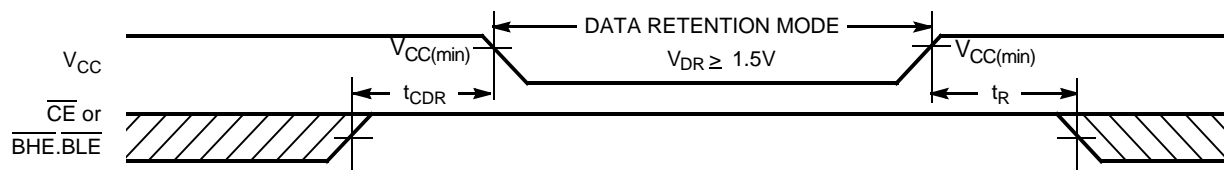
## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for Data Retention		1.5			V
$I_{CCDR}^{[7]}$	Data Retention Current	$V_{CC} = 1.5V, \overline{CE} \geq V_{CC} - 0.2V, V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	Ind'I/Auto-A		4	$\mu A$
			Auto-E		12	
$t_{CDR}^{[8]}$	Chip Deselect to Data Retention Time		0			ns
$t_R^{[9]}$	Operation Recovery Time		$t_{RC}$			ns

## Data Retention Waveform

**Figure 4. Data Retention Waveform<sup>[10]</sup>**



### Notes

8. Tested initially and after any design or process changes that may affect these parameters.
9. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)}$   $\geq 100 \mu s$  or stable at  $V_{CC(min)}$   $\geq 100 \mu s$ .
10. BHE.BLE is the AND of both BHE and BLE. Deselect the chip by either disabling chip enable signals or by disabling both  $\overline{BHE}$  and  $\overline{BLE}$ .

## Switching Characteristics

Over the Operating Range <sup>[11, 12]</sup>

Parameter	Description	45 ns (Ind'l/Auto-A)		55 ns (Auto-E)		Unit
		Min	Max	Min	Max	
Read Cycle						
t <sub>RC</sub>	Read Cycle Time	45		55		ns
t <sub>AA</sub>	Address to Data Valid		45		55	ns
t <sub>OHA</sub>	Data Hold From Address Change	10		10		ns
t <sub>ACE</sub>	$\overline{CE}$ LOW to Data Valid		45		55	ns
t <sub>DOE</sub>	$\overline{OE}$ LOW to Data Valid		22		25	ns
t <sub>LZOE</sub>	$\overline{OE}$ LOW to Low Z <sup>[13]</sup>	5		5		ns
t <sub>HZOE</sub>	$\overline{OE}$ HIGH to High Z <sup>[13, 14]</sup>		18		20	ns
t <sub>LZCE</sub>	$\overline{CE}$ LOW to Low Z <sup>[13]</sup>	10		10		ns
t <sub>HZCE</sub>	$\overline{CE}$ HIGH to High Z <sup>[13, 14]</sup>		18		20	ns
t <sub>PU</sub>	$\overline{CE}$ LOW to Power Up	0		0		ns
t <sub>PD</sub>	$\overline{CE}$ HIGH to Power Down		45		55	ns
t <sub>DBE</sub>	$\overline{BLE/BHE}$ LOW to Data Valid		45		55	ns
t <sub>LZBE</sub>	$\overline{BLE/BHE}$ LOW to Low Z <sup>[13, 15]</sup>	5		10		ns
t <sub>HZBE</sub>	$\overline{BLE/BHE}$ HIGH to High Z <sup>[13, 14]</sup>		18		20	ns
Write Cycle <sup>[16]</sup>						
t <sub>WC</sub>	Write Cycle Time	45		55		ns
t <sub>SCE</sub>	$\overline{CE}$ LOW to Write End	35		40		ns
t <sub>AW</sub>	Address Setup to Write End	35		40		ns
t <sub>HA</sub>	Address Hold from Write End	0		0		ns
t <sub>SA</sub>	Address Setup to Write Start	0		0		ns
t <sub>PWE</sub>	$\overline{WE}$ Pulse Width	35		40		ns
t <sub>BW</sub>	$\overline{BLE/BHE}$ LOW to Write End	35		40		ns
t <sub>SD</sub>	Data Setup to Write End	25		25		ns
t <sub>HD</sub>	Data Hold From Write End	0		0		ns
t <sub>HZWE</sub>	$\overline{WE}$ LOW to High Z <sup>[13, 14]</sup>		18		20	ns
t <sub>LZWE</sub>	$\overline{WE}$ HIGH to Low Z <sup>[13]</sup>	10		10		ns

### Notes

11. Test conditions for all parameters, other than tri-state parameters, assume signal transition time of 3 ns (1V/ns) or less, timing reference levels of  $V_{CC(typ)}/2$ , input pulse levels of 0 to  $V_{CC(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  as shown in "AC Test Loads and Waveforms" on page 4.
12. AC timing parameters are subject to byte enable signals (BHE or BLE) not switching when chip is disabled. Please see application note AN13842 for further clarification.
13. At any temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZBE</sub> is less than t<sub>LZBE</sub>, t<sub>HZOE</sub> is less than t<sub>LZOE</sub>, and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any device.
14. t<sub>HZOE</sub>, t<sub>HZCE</sub>, t<sub>HZBE</sub>, and t<sub>HZWE</sub> transitions are measured when the outputs enter a high impedance state.
15. If both byte enables are toggled together, this value is 10 ns.
16. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE} = V_{IL}$ ,  $\overline{BHE}$  and/or  $\overline{BLE} = V_{IL}$ . All signals are ACTIVE to initiate a write and any of these signals terminate a write by going INACTIVE. The data input setup and hold timing are referenced to the edge of the signal that terminates the write.

## Switching Waveforms

Figure 5. Read Cycle 1: Address Transition Controlled [17, 18]

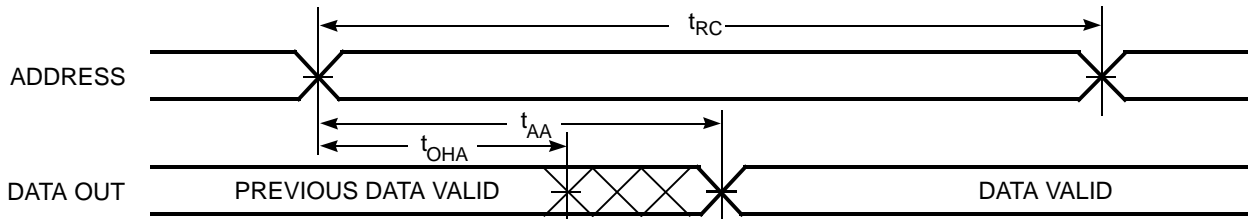
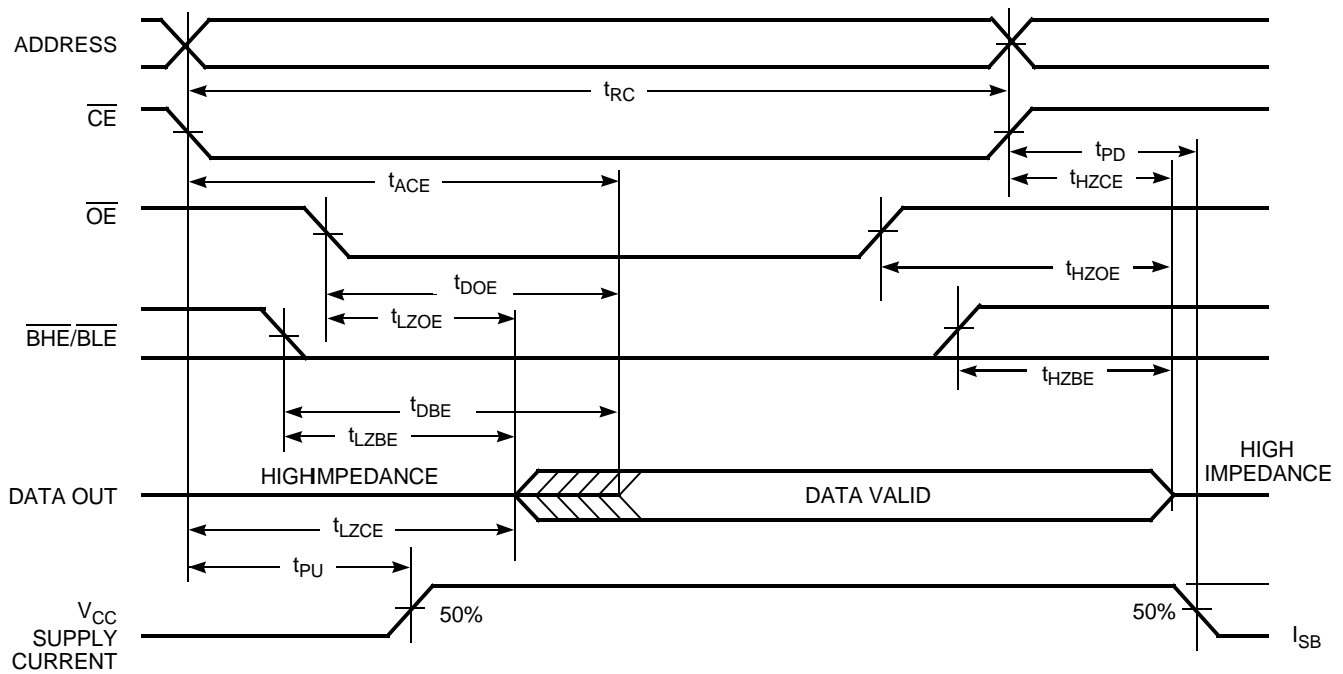


Figure 6. Read Cycle 2:  $\overline{\text{OE}}$  Controlled [18, 19]

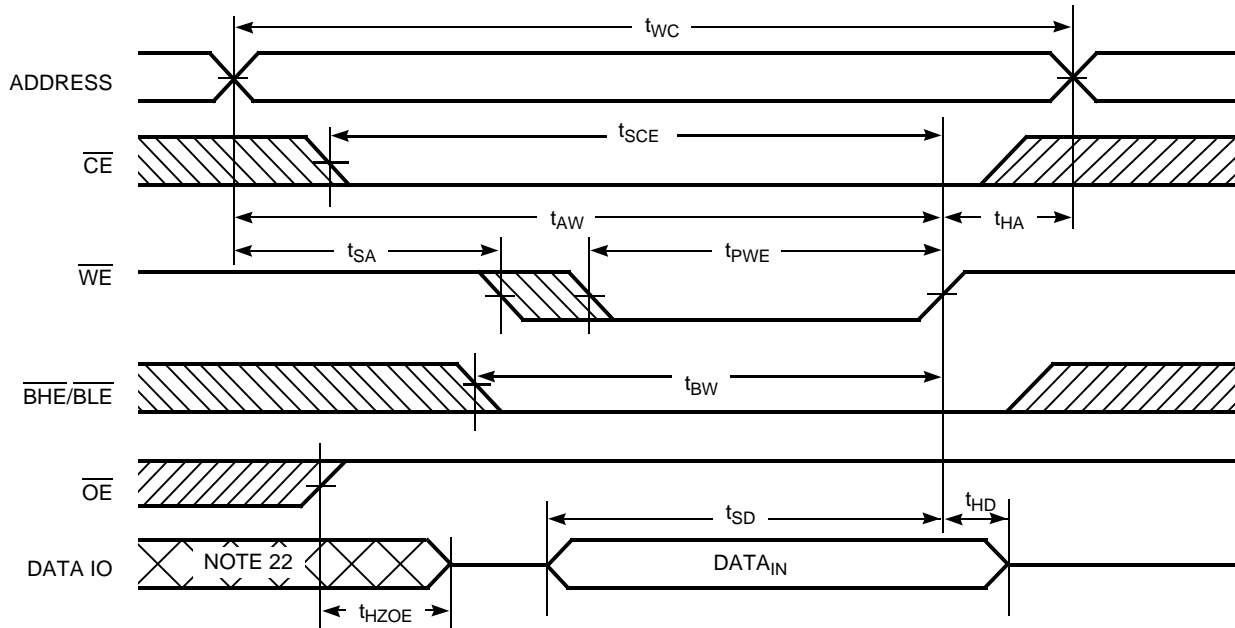
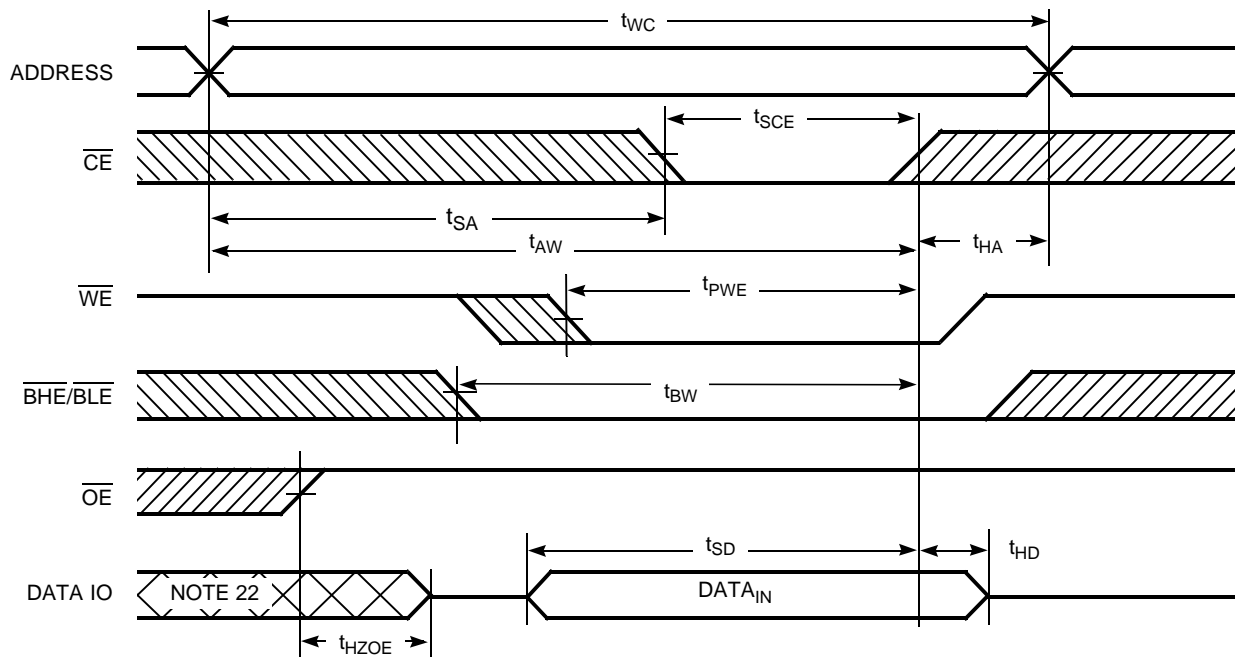


### Notes

17. The device is continuously selected.  $\overline{\text{OE}}$ ,  $\overline{\text{CE}} = V_{\text{IL}}$ ,  $\overline{\text{BHE}}$  and/or  $\overline{\text{BLE}} = V_{\text{IL}}$ .

18.  $\overline{\text{WE}}$  is HIGH for read cycle.

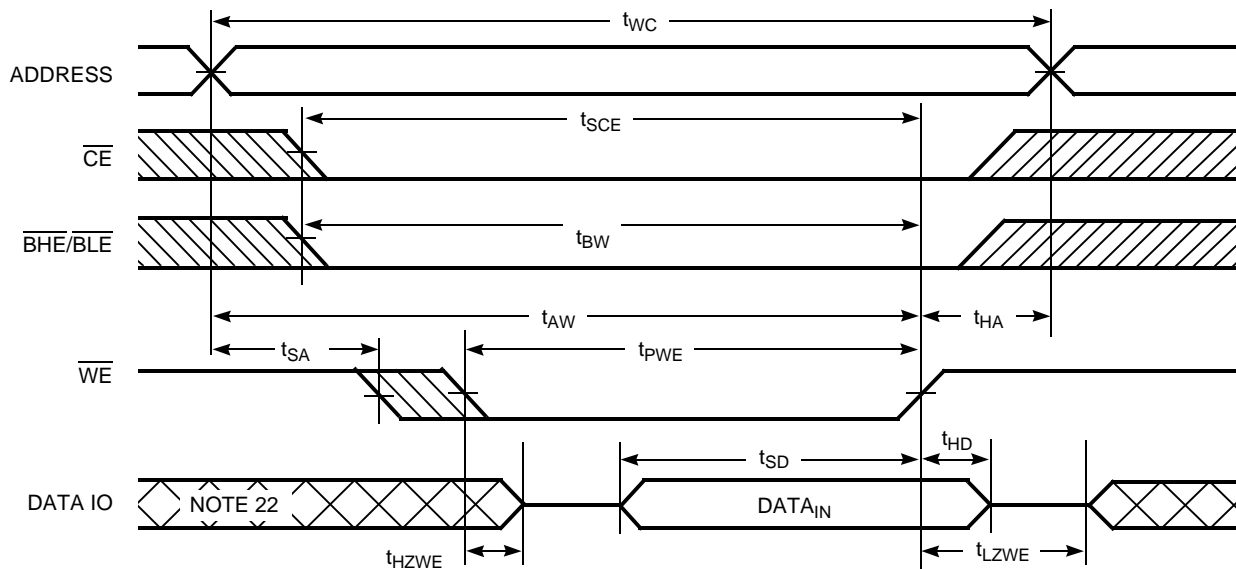
19. Address valid before or similar to  $\overline{\text{CE}}$  and  $\overline{\text{BHE}}$ ,  $\overline{\text{BLE}}$  transition LOW.

**Switching Waveforms (continued)**
**Figure 7. Write Cycle 1:  $\overline{\text{WE}}$  Controlled** [16, 20, 21]

**Figure 8. Write Cycle 2:  $\overline{\text{CE}}$  Controlled** [16, 20, 21]

**Notes**

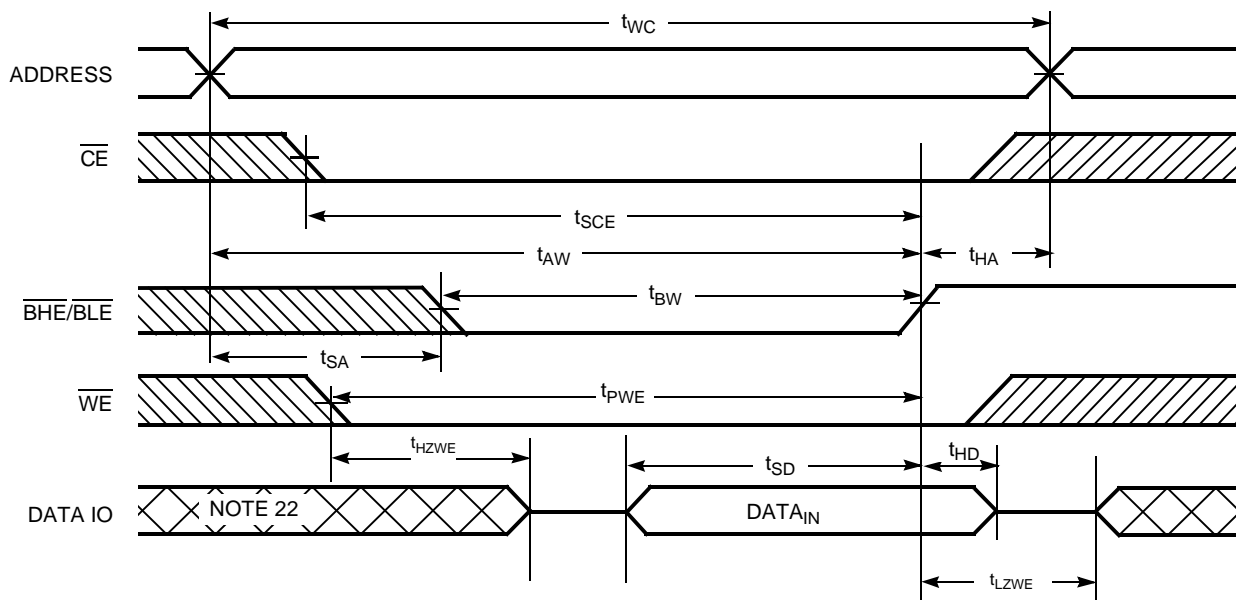
20. Data IO is high impedance if  $\overline{\text{OE}} = V_{IH}$ .
21. If CE goes HIGH simultaneously with  $\text{WE} = V_{IH}$ , the output remains in a high impedance state.
22. During this period, the IOs are in output state. Do not apply input signals.

## Switching Waveforms (continued)

**Figure 9. Write Cycle 3:  $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW <sup>[21]</sup>**



**Figure 10. Write Cycle 4:  $\overline{\text{BHE/BLE}}$  Controlled,  $\overline{\text{OE}}$  LOW <sup>[21]</sup>**





**Truth Table**

<b><math>\overline{CE}</math></b>	<b><math>\overline{WE}</math></b>	<b><math>\overline{OE}</math></b>	<b><math>\overline{BHE}</math></b>	<b><math>\overline{BLE}</math></b>	<b>Inputs or Outputs</b>	<b>Mode</b>	<b>Power</b>
H	X	X	X	X	High Z	Deselect or Power Down	Standby ( $I_{SB}$ )
X	X	X	H	H	High Z	Deselect or Power Down	Standby ( $I_{SB}$ )
L	H	L	L	L	Data Out ( $IO_0$ – $IO_{15}$ )	Read	Active ( $I_{CC}$ )
L	H	L	H	L	Data Out ( $IO_0$ – $IO_7$ ); $IO_8$ – $IO_{15}$ in High Z	Read	Active ( $I_{CC}$ )
L	H	L	L	H	Data Out ( $IO_8$ – $IO_{15}$ ); $IO_0$ – $IO_7$ in High Z	Read	Active ( $I_{CC}$ )
L	H	H	L	L	High Z	Output Disabled	Active ( $I_{CC}$ )
L	H	H	H	L	High Z	Output Disabled	Active ( $I_{CC}$ )
L	H	H	L	H	High Z	Output Disabled	Active ( $I_{CC}$ )
L	L	X	L	L	Data In ( $IO_0$ – $IO_{15}$ )	Write	Active ( $I_{CC}$ )
L	L	X	H	L	Data In ( $IO_0$ – $IO_7$ ); $IO_8$ – $IO_{15}$ in High Z	Write	Active ( $I_{CC}$ )
L	L	X	L	H	Data In ( $IO_8$ – $IO_{15}$ ); $IO_0$ – $IO_7$ in High Z	Write	Active ( $I_{CC}$ )

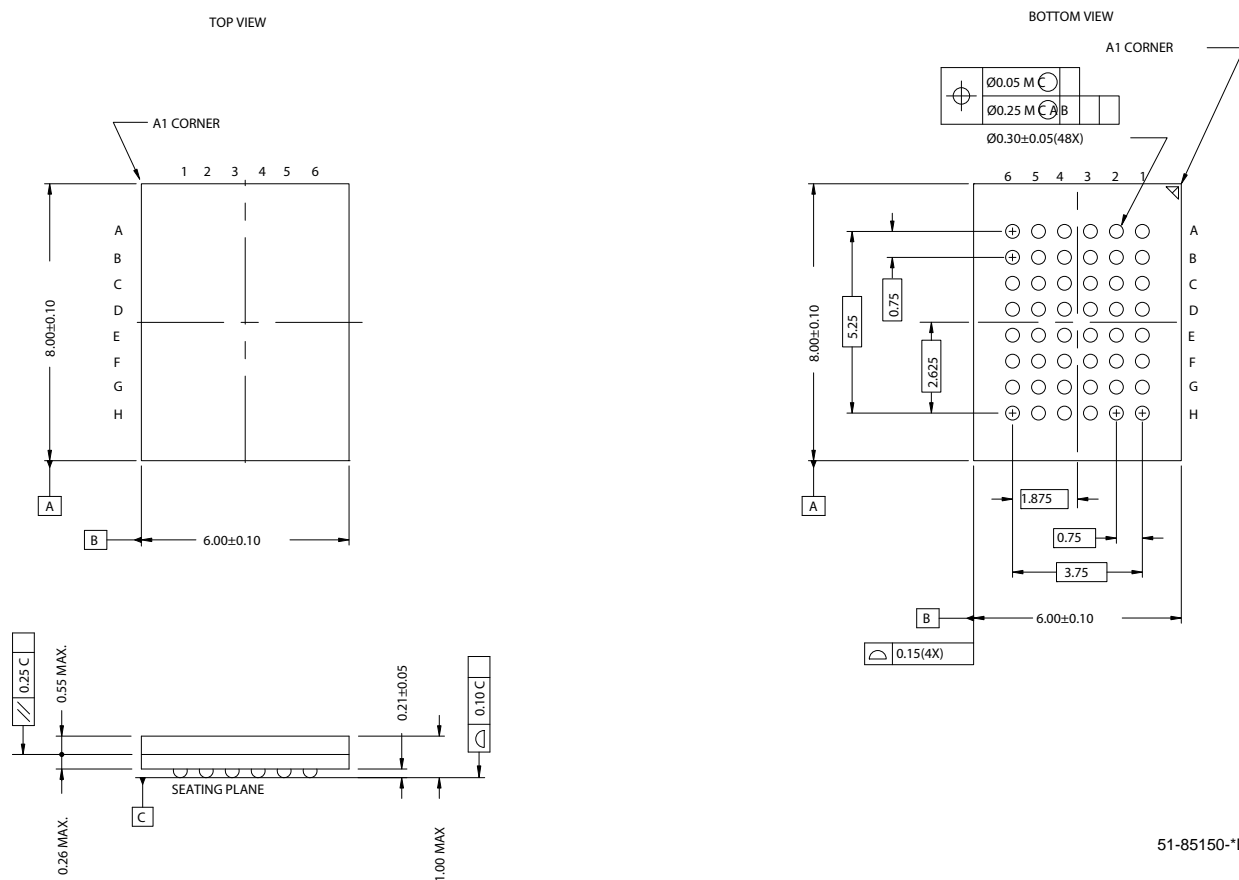
## Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62137FV30LL-45BVI	51-85150	48-Ball VFBGA	Industrial
	CY62137FV30LL-45BVXI		48-Ball VFBGA (Pb-free)	
	CY62137FV30LL-45ZSXI	51-85087	44-Pin TSOP II (Pb-free)	
45	CY62137FV30LL-45ZSXA	51-85087	44-Pin TSOP II (Pb-free)	Automotive-A
55	CY62137FV30LL-55ZSXE	51-85087	44-Pin TSOP II (Pb-free)	Automotive-E

Contact your local Cypress sales representative for availability of these parts.

## Package Diagram

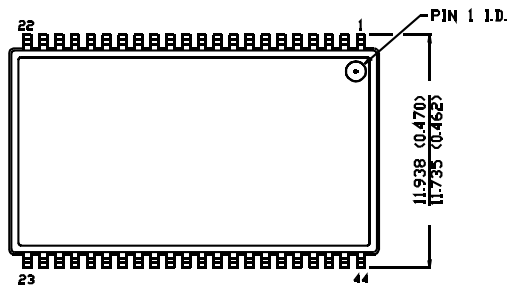
**Figure 11. 48-Ball VFBGA (6 x 8 x 1 mm)**



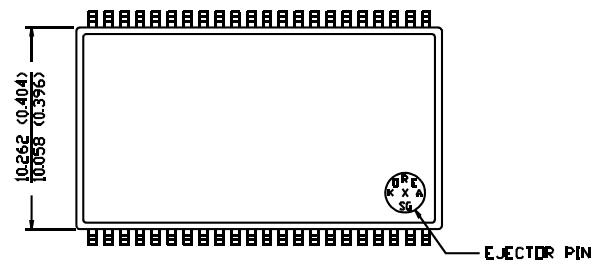
**Package Diagram (continued)**

**Figure 12. 44-Pin TSOP II**

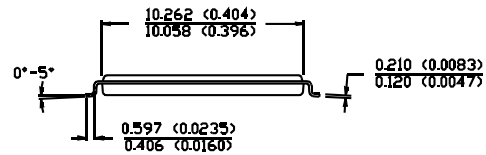
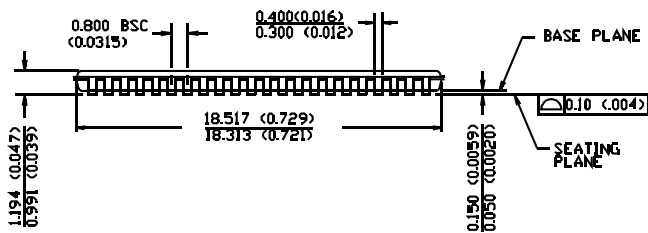
DIMENSION IN MM (INCH)  
MAX  
MIN



**TOP VIEW**



**BOTTOM VIEW**



51-85087-\*A

## Document History Page

Document Title: CY62137FV30 MoBL® 2-Mbit (128K x 16) Static RAM Document Number: 001-07141				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	449438	See ECN	NXR	New datasheet
*A	464509	See ECN	NXR	Changed the $I_{SB2(typ)}$ value from 1.0 $\mu A$ to 0.5 $\mu A$ Changed the $I_{SB2(max)}$ value from 4 $\mu A$ to 2.5 $\mu A$ Changed the $I_{CC(typ)}$ value from 2 mA to 1.6 mA and $I_{CC(max)}$ value from 2.5 mA to 2.25 mA for $f=1$ MHz test condition Changed the $I_{CC(typ)}$ value from 15 mA to 13 mA and $I_{CC(max)}$ value from 20 mA to 18 mA for $f=1$ MHz test condition Changed the $I_{CCDR(typ)}$ value from 0.7 $\mu A$ to 0.5 $\mu A$ and $I_{CCDR(max)}$ value from 3 $\mu A$ to 2.5 $\mu A$
*B	566724	See ECN	NXR	Converted from preliminary to final Changed the $I_{CC(max)}$ value from 2.25 mA to 2.5 mA for test condition $f=1$ MHz Changed the $I_{SB2(typ)}$ value from 0.5 $\mu A$ to 1 $\mu A$ Changed the $I_{SB2(max)}$ value from 2.5 $\mu A$ to 5 $\mu A$ Changed the $I_{CCDR(typ)}$ value from 0.5 $\mu A$ to 1 $\mu A$ and $I_{CCDR(max)}$ value from 2.5 $\mu A$ to 4 $\mu A$
*C	869500	See ECN	VKN	Added Automotive-A and Automotive-E information Updated Ordering Information Table Added footnote 13 related to $t_{ACE}$
*D	901800	See ECN	VKN	Added footnote 9 related to $I_{SB2}$ and $I_{CCDR}$ Made footnote 14 applicable to AC parameters from $t_{ACE}$
*E	1371124	See ECN	VKN/AESA	Converted Automotive information from preliminary to final Changed $I_{IX}$ min spec from -1 $\mu A$ to -4 $\mu A$ and $I_{IX}$ max spec from +1 $\mu A$ to +4 $\mu A$ Changed $I_{OZ}$ min spec from -1 $\mu A$ to -4 $\mu A$ and $I_{OZ}$ max spec from +1 $\mu A$ to +4 $\mu A$
*F	1875374	See ECN	VKN/AESA	Added -45BVI part in the Ordering Information table

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